

Rad-hard plastic quad 2-input NAND gate



Features

- NAND gate
- 1.65 V to 6 V operating supply
- 7 V max. rating
- 8 ns propagation delay
- Nickel/palladium/gold-lead-finished (NiPdAu), whisker-free
- · Gold-wires
- RML < 1% and CVCM < 0.1% guaranteed outgassing
- 50 krad (Si) total ionizing dose
- SEL-free up to 62.5 MeV.cm²/mg
- Mass: 80 mg
- Compliant with ST-LEO-specification

Product status link

LEOAC00

Application

· Low earth orbit (LEO) applications

Description

The LEOAC00 is a CMOS low power quad 2-input NAND gate qualified for use in aerospace environments. It operates from 1.65 V to 6 V power supply (7 V absolute maximum ratings).

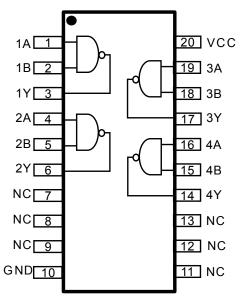
The LEOAC00 can operate over a large temperature range of -40 °C to +125 °C and it is housed in plastic TSSOP-20, thin-shrink small outline package, 20 leads, using gold-wires and nickel/palladium/golden-lead-finishing to prevent from whiskers.

The LEOAC00 is compliant with ST-LEO-specification, dedicated specification for space-ready rad-hard plastic products. This AEC-Q100-based specification offers a specific trade-off between footprint size savings, cost of ownership and quality assurance together with radiation hardness and large quantity capability.



1 Functional description

Figure 1. Pin connections (top view)



NC: not internally connected.

The pin can be externally connected to any potential.

Table 1. Truth table

Each gate					
INPUT (A)	INPUT (B)	OUTPUT (Y)			
L	L	Н			
L	Н	Н			
Н	L	Н			
Н	Н	L			

with: L = low level, H = high Level.

For all inputs, VIN = VIH minimum or VIL maximum, verify output VOUT.

DS13639 - Rev 5 page 2/17



2 Maximum ratings and operating conditions

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
VCC ⁽¹⁾	Maximum power supply between VCC and GND	-0.5 to 7	V
VIN	DC input voltage range	-0.5 to VCC+0.5 (and 7 V max.)	V
VOUT	DC output voltage range	-0.5 to VCC+0.5 (and 7 V max.)	V
IK	I/O clamp diode current	+/-20	mA
T _{stg}	Maximum temperature storage	-65 to 150	°C
T _j ⁽²⁾	Maximum junction temperature	+150	°C
Rth ⁽³⁾	Junction-to-ambient thermal resistance (Θja)	80	°C/W
Run	Junction-to-case thermal resistance (Θjc)	17	°C/W
ESD	HBM (human body model)	2 k	V
LOD	CDM (charged device model)	1 k	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \

- 1. All voltages, except differential I/O bus voltage, are with respect to the network ground terminal.
- 2. Maximum junction temperature shall not be exceeded except for allowable short duration burn-in screening conditions as per the method 5004 of MIL-STD-883.
- 3. Short-circuits can cause excessive heating. Destructive dissipation can result from short-circuits on the amplifiers.

Note:

Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. All values are referred to GND.

Table 3. Operating conditions

Symbol	Parameter	Min.	Max.	Unit
VCC	Analog supply voltage	1.65	6	V
VIN	Input voltage range	0	VCC	V
VOUT	Output voltage range	0	VCC	V
T _a	Ambient temperature range	-40	+125	°C

Note: All unused inputs must be held at VCC or GND to ensure proper device operation.

DS13639 - Rev 5 page 3/17



3 Electrical characteristics

VCC = 3 V to 5.5 V, typical values are at ambient T_a = +25 °C, minimum and maximum values are at T_a = -40 °C and +125 °C, unless otherwise specified.

Table 4. Electrical characteristics

For all inputs affecting output under test, VIN = VIH minimum or VIL maximum. For all other inputs, VIN = VCC or GND, IOH = -50 µA	Symbol	Parameter	Test conditions	VCC	Min.	Тур.	Max.	Unit	
VOH 10 VOH 10 VOC or GND, IOH = -50 μA 5.5 V 5.4				3 V	2.9				
VOH (1)			·	4.5 V	4.4				
VOH 10			VIN = VCC or GND, IOH = -50 μA		5.4				
For all inputs affecting output under test, VIN = VIH minimum or VIL maximum. For all other inputs, VIN = VCC or GND, IOH = -24 mA 5.5 V 4.7 5.5 V 5	VOH (1)	High level output voltage	minimum or VIL maximum. For all other inputs, VIN =	3 V	2.4			V	
VIN = VCC or GND, IOH = -24 mA 5.5 V 4.7	VOIT	riigii level oalpat voltage		4.5 V	3.7			ľ	
Minimum or VIL maximum. For all other inputs, VIN = VCC or GND IOH = -50 mA 3 V 0.1				5.5 V	4.7				
VOL ⁽¹⁾ Low level output voltage For all inputs affecting output under test, VIN = VIH minimum or VIL maximum. For all other inputs, V			minimum or VIL maximum. For all other inputs,	5.5 V	3.85				
VOL(1) VOL(1) VOC or GND, IOL = +50 µA 5.5 V 0.1			VIN = VCC OF GND IOH = -50 MA	2.1/			0.4		
VOL(1) VOR = VCC or GND, IOL = +50 μA 5.5 V 0.1		Low level output voltage							
VOL(1) Low level output voltage For all inputs affecting output under test, VIN = VIH minimum or VIL maximum. For all other inputs, VIN = VCC or GND, IOL = +12 mA For all inputs affecting output under test, VIN = VIH minimum or VIL maximum. For all other inputs, VIN = VCC or GND, IOL = +24 mA For all inputs affecting output under test, VIN = VIH minimum or VIL maximum. For all other inputs, VIN = VCC or GND, IOL = +24 mA For all inputs affecting output under test, VIN = VIH minimum or VIL maximum. For all other inputs, VIN = VCC or GND, IOL = +50 mA 3 V	VOL ⁽¹⁾		·						
NOL(1) Low level output voltage Low level input voltage Low level output voltage Low level input voltage Low level output voltage Low level input volt			,	5.5 V			0.1		
For all inputs affecting output under test, VIN = VIH minimum or VIL maximum. For all other inputs, VIN = VCC or GND, IOL = +24 mA 5.5 V 0.5			minimum or VIL maximum. For all other inputs,	3 V			0.5	V	
minimum or VIL maximum. For all other inputs, VIN = VCC or GND, IOL = +24 mA 5.5 V 0.5			·	4 = > 1			0.5		
VIN = VCC or GND, IOL = +24 INA			, ,	4.5 V			0.5		
Minimum or VIL maximum. For all other inputs,			VIN = VCC or GND, IOL = +24 mA	5.5 V			0.5		
IOH High level output current 3 \ \ -12			minimum or VIL maximum. For all other inputs,	5.5 V			1.65		
IOH High level output current 4.5 V -24			VIIV - VOC OF GIVE, TOE - 130 TIE	3 \/	-12				
Solution	IOH	High level output current							
3 V 12	1011	riigiriever output current							
VIH High level input voltage 4.5 V 24				-	-2-		12	mA	
VIH High level input voltage 3 V 2.1 VIL 4.5 V 3.15 5.5 V 3.85 VIL Low level input voltage 3 V 0.9 4.5 V 1.35 5.5 V 1.65	IOI	Low level output current							
VIH High level input voltage 3 V 2.1	102	Low lovel output outlone							
VIH High level input voltage 4.5 V 3.15 5.5 V 3.85 VIL Low level input voltage 4.5 V 0.9 4.5 V 1.35 5.5 V 1.65					21		27		
VIL Low level input voltage 5.5 V 3.85 3 V 0.9 4.5 V 1.35 5.5 V 1.65	VIH	High level input voltage							
VIL Low level input voltage 3 V 0.9 4.5 V 1.35 5.5 V 1.65		J							
VIL Low level input voltage 4.5 V 1.35 5.5 V 1.65					5.00		0.9	V	
5.5 V 1.65	VIL	Low level input voltage							
	· -	, , , , , , , , , , , , , , , , , , , ,							
VIC+ Positive input clamp voltage For input under test, IIN = 1 mA	VIC+	Positive input clamp	For input under test,		0.4			V	

DS13639 - Rev 5 page 4/17



Symbol	Parameter	Test conditions	vcc	Min.	Тур.	Max.	Unit
VIC-	Negative input clamp voltage	For input under test, IIN = -1.0 mA	Open	-0.4		-1.5	V
		For input under test, VIN = VCC					
IIH	Input current high	For all other inputs,	5.5 V			1	μA
		VIN = VCC or GND					
		For input under test, VIN = GND					
IIL	Input current low	For all other inputs,	5.5 V			-1	μA
		VIN = VCC or GND					
ICCH	Quiescent supply	For all inputs, VIN = VCC or GND	5.5 V			40	μA
	current, output high	IOUT = 0 A	0.0 1			10	μ/ (
ICCL	Quiescent supply	For all inputs, VIN = VCC or GND	5.5 V			40	μA
IOOL	current, output low	IOUT = 0 A	3.5 V			40	μΛ
CIN ⁽²⁾	Input capacitance	Ta=+25°C	5 V			10	pF
CPD ⁽²⁾⁽³⁾	Power dissipation capacitance	Ta=+25°C, F = 1 MHz	5 V			50	pF
		CL = 2 pF, RL = 500 ohm,	3 V		3.3		
T_r , T_f	Output rise time and fall	see Figure 2. Waveform	4.5		2.7		
'r, 'f	time	CL = 2 pF, RL = 500 ohm,	3 V		4.6		ns
		see Figure 2. Waveform	4.5 V		3.3		
t _{PHL} ⁽⁴⁾	Propagation delay time	CL = 50 pF, RL = 500 ohm	3 V	1		9.5	
	An to Yn, high to low	See Figure 2. Waveform	4.5 V	1		8	1
	Propagation delay time	CL = 50 pF, RL = 500 ohm	3 V	1		9.5	ns
t _{PLH} ⁽⁴⁾	An to Yn, low to high	See Figure 2. Waveform	4.5 V	1		8	1

- 1. The VOH and VOL tests shall be tested at VCC = 3.0 V and 4.5 V. The VOH and VOL tests are guaranteed, if not tested, for other values of VCC. Limits shown apply to operation at VCC = 3.3 V ±0.3 V and VCC = 5.0 V ±0.5 V. Tests with input current at +50 mA and -50 mA are performed on only one input at a time with duration not to exceed 10 ms. Transmission driving tests may be performed using VIN = VCC or GND. When VIN = VCC or GND is used, the test is guaranteed for VIN = VIH minimum and VIL maximum.
- 2. CIN and CPD shall be measured only for initial qualification and after process or design changes which may affect capacitance. CIN shall be measured between the designated terminal and GND at a frequency of 1 MHz. CPD shall be tested in accordance with the latest revision of JEDEC standard JESD20 and table IA herein. For CIN and CPD, test all applicable pins on five devices with zero failures.
- 3. Power dissipation capacitance (CPD) determines both the power consumption (PD) and dynamic current consumption (IS). Where: PD = (CPD + CL) (VCC x VCC) f + (ICC x VCC) and IS = (CPD + CL) VCC x f + ICC, and f is the frequency of the input signal and CL is the external output load capacitance.
- 4. The AC limits at VCC = 5.5 V are equal to the limits at VCC = 4.5 V and guaranteed by testing at VCC = 4.5 V. The AC limits at VCC = 3.6 V are equal to the limits at VCC = 3.0 V and guaranteed by testing at VCC = 3.0 V. Minimum AC limits for VCC = 5.5 V and VCC = 3.6 V are 1.0 ns and guaranteed by guard banding the VCC = 4.5 V and VCC = 3.0 V minimum limits, respectively, to 1.5 ns. For propagation delay tests, all paths must be tested.

DS13639 - Rev 5 page 5/17



4 Waveform and test circuit

Figure 2. Waveform

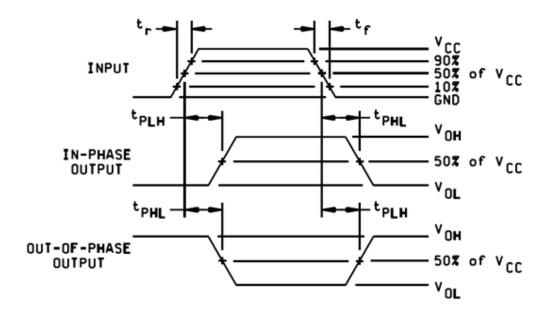
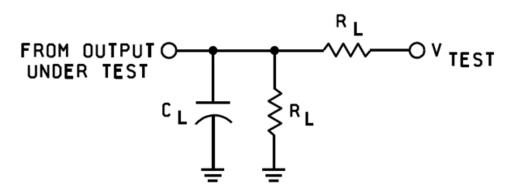


Figure 3. Test circuit



Note:

- When measuring t_{PHL} or t_{PLH} : VTEST = open.
- CL = 50 pF minimum or equivalent (includes probe and jig capacitance).
- $RL = 500 \Omega$ or equivalent.
- Input signal from pulse generator: VIN = 0.0 V to VCC; PRR \leq 1 MHz; ZO = 50 Ω ; tr \leq 3.0 ns; tf \leq 3.0 ns; tr and t_f shall be measured from 10% of VCC to 90% of VCC and from 90% of VCC to 10% of VCC, respectively; duty cycle = 50 percent.
- Timing parameters shall be tested at a minimum input frequency of 1 MHz.
- The outputs are measured one at a time with one transition per measurement.

DS13639 - Rev 5 page 6/17



5 Radiations

Total ionizing dose (TID):

For the qualification, the product is characterized in TID as per MIL-STD-883 TM 1019 up to 50 krad (Si) on 5 biased parts at high dose rate, such a rate being the worst condition for a pure CMOS technology.

All parameters provided in Table 4. Electrical characteristics apply to both pre- and post-irradiation.

Each new production lot is tested at high dose rate as per MIL-STD-883 TM 1019 on 5 parts.

Heavy-ions:

Single event latchup (SEL) is characterized at 125 °C at a LET of 62.5 MeV.cm2/mg. The test shows the product is immune to heavy ions at this LET. Heavy-ion trials are performed on qualification lots only.

The results in radiation are summarized in Table 5 as follows:

Table 5. Radiations

Symbol	Characteristics	Value
TID	 High-dose rate (40 krad (Si) / h) Temperature: 25 °C Performed on 5 biased parts 	Within Table 4 up to 50 krad (Si)
SEL	 LET: 62.5 MeV.cm2/mg (Xenon ions) Temperature: 125 °C Fluence: 1 x 10⁷ ions/cm² (10 million of particles per cm²) Normal incidence 	Immune to SEL up to 62.5 MeV.cm ² /mg

^{1.} A total ionizing dose (TID) of 50 krad(Si) is equivalent to 500 Gy(Si), (1 gray = 100 rad).

2. SEL: single event latch-up.

DS13639 - Rev 5 page 7/17



6 Outgassing

Specification (tested per ASTM E 595)	Value	Unit
Recovered mass loss (RML) ⁽¹⁾	0.06	%
Collected volatile condensable material (CVCM) ⁽²⁾	0.00	%

- 1. RML < 1%.
- 2. CVCM < 0.1%.

DS13639 - Rev 5 page 8/17



7 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

7.1 TSSOP-20 package information

Figure 4. TSSOP-20 package outline

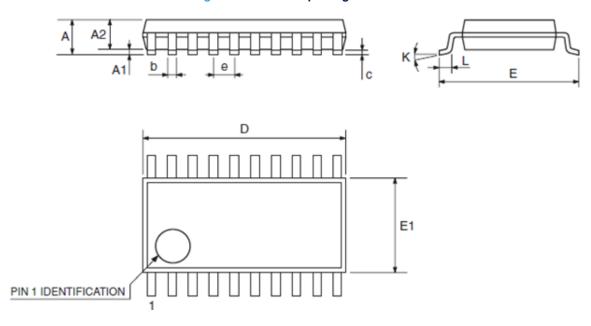


Table 6. TSSOP-20 package mechanical data

Symbol		Milimeters			Inches ⁽¹⁾	
Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.
А			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		
С	0.09		0.20	0.004		
D	6.4	6.5	6.6	0.252	0.256	0.260
Е	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
е		0.65 BSC			0.0256 BSC	
К	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

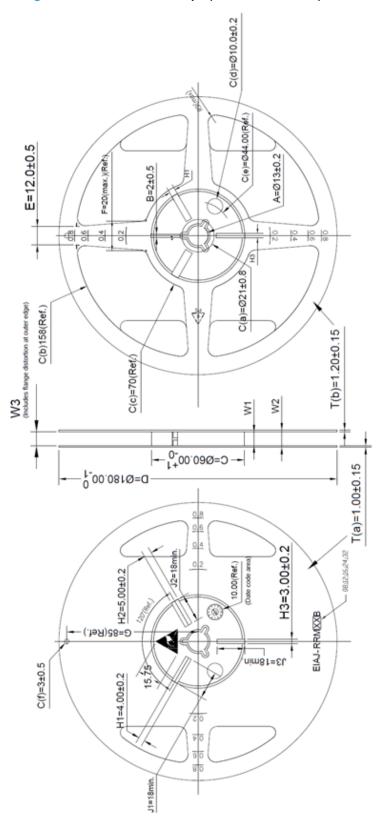
Note: TSSOP: Thin-Shrink Small Outline Package, using golden bonding and Nickel/Palladium/Golden-lead-finishing.

DS13639 - Rev 5 page 9/17

7.2

TSSOP-20 packing information

Figure 5. TSSOP-20 Carrier tape (dimensions in mm) outline



DS13639 - Rev 5 page 10/17



16.0 ±.3 1.75 ±.10 Ф Ф Φ SECTION B - B Ф Ø 1.5 +0.1/-0.0 \oplus Ф \oplus 0 R 0.3 T/P. Ø 1.50 MIN Ф \oplus 0 6.95 1.80 1.80 1.20 \oplus 7888 |----¥ 8.00 Ф 0 0 \oplus 2.00 ±.10 SE NOTE 3 — 4.00 SE NOTE 1 — NOTES:
1. 10 SPROCKET HOLE PLTCH CUMLATIVE TOLERANCE ±0.2
2. CANGER IN COMPLIANCE WITH EIA 481
3. POCKET POSTITION RELATIVE TO SPROCKET HOLE MEASURED
AS TRUE POSTITION OF POCKET, NOT POCKET HOLE 9. 9. 8 SECTION A -T ±.05 R 0.3 MAX

Figure 6. TSSOP-20 tape (dimensions in mm) outline

DS13639 - Rev 5 page 11/17



8 Ordering information

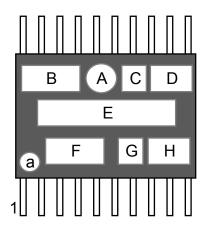
Table 7. Ordering information

Order code	Quality level	Package	Lead-finish	Marking	Packing
LEOAC00PT-D	Development sample	TSSOP-20	NiPdAu	DLEOAC00	Tape and reel
LEOAC00PT	Flight model	TSSOP-20	NiPdAu	LEOAC00	Tape and reel

Table 8. Order code

LEO	AC00	Р	Т
LEO qualification	Name	TSSOP-20 package	Tape and reel

Figure 7. TSSOP-20 marking



- a: pin-1 reference
- A: Second Level of interconnexion (type of lead-finishing)
- B: ST logo
- C: Assy plant
- D: Lot code
- E: Marking area
- F: Country of origin
- G: Assy year
- H: Assy week

DS13639 - Rev 5 page 12/17



Revision history

Table 9. Document revision history

Date	Version	Changes
10-Feb-2021	1	Initial release.
29-Mar-2021	2	Updated Section 8 Ordering information. Removed "product documentation" section.
08-Jun-2021	3	Updated T _{STG} value in Table 2 and T _{ID} characteristics in Table 5.
30-Aug-2021	4	Updated Section 5 Radiations.
04-Oct-2024	5	Updated minimum operating power supply from 2 V to 1.65 V.

DS13639 - Rev 5 page 13/17



Contents

1	Fun	ctional description	2			
2	Max	kimum ratings and operating conditions	3			
3	Elec	ctrical characteristics	4			
4	Wav	eform and test circuit	6			
5	Rad	liations	7			
6	Outgassing					
7	Pac	kage information	9			
	7.1	TSSOP-20 package information	9			
	7.2	TSSOP-20 packing information	. 10			
8	Ord	ering information	.12			
Re	vision	history	.13			



List of tables

Table 1.	Truth table	2
Table 2.	Absolute maximum ratings	3
Table 3.	Operating conditions	3
Table 4.	Electrical characteristics	4
Table 5.	Radiations	7
Table 6.	TSSOP-20 package mechanical data	9
Table 7.	Ordering information	12
Table 8.	Order code	12
Table 9.	Document revision history	13



List of figures

Figure 1.	Pin connections (top view)	2
Figure 2.	Waveform	6
Figure 3.	Test circuit	6
Figure 4.	TSSOP-20 package outline	9
Figure 5.	TSSOP-20 Carrier tape (dimensions in mm) outline	10
Figure 6.	TSSOP-20 tape (dimensions in mm) outline	11
Figure 7.	TSSOP-20 marking	12

DS13639 - Rev 5



IMPORTANT NOTICE - READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgment.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, refer to www.st.com/trademarks. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2024 STMicroelectronics – All rights reserved

DS13639 - Rev 5 page 17/17